

WAFER PROCESSING METHOD

ABSTRACT OF THE DISCLOSURE

A wafer processing method for processing a wafer with devices formed in regions on a side of a front surface of the wafer, the regions being defined by first scheduled division lines and second scheduled division lines includes a first modified layer forming step and a second modified layer forming step. In the first modified layer forming step, a laser beam is irradiated with its focal point set at a height leveled with a height of a first region located inside the wafer on the side of the front surface of the wafer, whereby first modified layers are formed. In the second modified layer forming step, the laser beam is irradiated with its focal point set at a height leveled with a height of a second region located inside the wafer on a side of a back surface of the wafer, whereby second modified layers are formed.

[Fig. 3A]